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# Table of Contents

<b>Business Outlook for the Non-Volatile Memory Market .....</b>	<b>1</b>
<i>Alan Niebel</i>	
<b>MirrorBit' Technology Past, Present and Future: The On-going Scaling of Nitride-based Flash Memory.....</b>	<b>3</b>
<i>No Author</i>	
<b>Future Outlook of NAND Flash Technology for 40nm Node and Beyond .....</b>	<b>4</b>
<i>Kinam Kim, Jungdal Choi</i>	
<b>Chalcogenide Phase Change Memory: Scalable NVM for the Next Decade? .....</b>	<b>7</b>
<i>Roberto Bez and Greg Atwood</i>	
<b>NeoFlash® - True Logic Single Poly Flash Memory Technology.....</b>	<b>10</b>
<i>H. M. Lee, S. T. Woo, H. M. Chen, R. Shen, C. D. Wang, L.C. Hsia and C. C.-H. Hsu</i>	
<b>A High Performance Controller for NAND Flash-based Solid State Disk (NSSD).....</b>	<b>12</b>
<i>Chanik Park, Prakash Talawar, Daesik Won, MyungJin Jung, JungBeen Im, Suksan Kim and Youngjoon Choi</i>	
<b>Novel Buried Bitline Integration for compact Cell Design in High-Performance em-bedded Flash Memory with Deep Trench Isolation.....</b>	<b>16</b>
<i>A.T. Tilke, L. Pescini, M. Stiftinger, R. Kakoschke, D. Shum, N. Chan, S.R. Kim, K.J. Han</i>	
<b>A Novel Embedded OTP NVM Using Standard Foundry CMOS Logic Technology .....</b>	<b>19</b>
<i>J.Peng, G. Rosendale, M. Fliesler, D. Fong, J. Wang, C. Ng, ZS Liu, Harry Luan</i>	
<b>Embedded Non-Volatile Memory Modules for Low Voltage and High Temperature Applications.....</b>	<b>22</b>
<i>Jagdish Pathak, Mammen Thomas, Jim Payne, Gregor Schatzberger, Andreas Wiesner, Friedrich Leisenberger, Ewald Wachmann and Martin Schrems</i>	
<b>A New Programmig Disturbance Phenomenon in NANS Flash Memory by Sourx/Drain Hot-Electrons Generated by GIDL Current.....</b>	<b>26</b>
<i>Jae-Duk Lee, Chi-Kyung Lee, Myung-Won Lee, Han-Soo Kim, Kyu-Charn Park, and Won-Seong Lee</i>	
<b>A High Cost-Performance and Reliable 3-Level MLC NAND Flash Memory Using Virtual Page Cell Architecture .....</b>	<b>29</b>
<i>Ki-Tae Park, Jungdal Choi, Sungkyu Cho, Yunho Choi, Kinam Kim</i>	
<b>The Air Spacer Technology for Improving the Cell Distribution in 1 Giga Bit NAND Flash Memory.....</b>	<b>31</b>
<i>Daewoong Kang, Hyungcheol Shin, Sungnam Chang, Jungjoo An, Kyongjoo Lee, Jinjoo Kim, Eunsang Jeong, Hyukje Kwon, Eunjung Lee, Seunggun Seo, and Wonseong Lee</i>	
<b>New Cell Structure with Edge-thick Tunnel Oxide for Highly Reliable NAND Flash Memory Devices.....</b>	<b>33</b>
<i>Tae-Kyung Kim, Jaihyuk Song, Changsub Lee, Dongyeon Oh, Taeseok Jang, Jongkwang Lim, Dongjun Lee, Seungjun Lee, Minhwan Lim, Hyunyoung Shim, Bongtae Park, Man-Ki Lee, Hunkook Lee, Sangyeon Jo, Woonkyung Lee, Jeonghyuk Choi and Kinam Kim</i>	
<b>Effect of Source Diffusion on SILC and Cycling-Induced Charge Loss in Source-Bias Erase Flash Cells .....</b>	<b>35</b>
<i>Chun Chen, Jeff Kessenich, Paul Rudeck, Ramin Ghodsi, Wayne Kinney, Andrew Bicksler, Kirk Prall, Lee Nevill, and Andrei Mihnea</i>	
<b>Reliability and Qualification of a Floating Gate Memory Manufactured in a Generic Logic Process for RFID Applications.....</b>	<b>39</b>
<i>Yanjun Ma, Alberto Pesavento, Hoc Nguyen, Haibo Li, and Ron Paulsen</i>	
<b>Ultra-Short Pulses Improving Performance and Reliability in Flash Memories.....</b>	<b>41</b>
<i>Andrea Chimenton, Fernanda Irrera and Piero Olivo</i>	
<b>Performance and Reliability of 2-Transistor FN/FN Flash Arrays with Hafnium Based High-K Inter-Poly Dielectrics for Embedded NVM .....</b>	<b>43</b>
<i>M. van Duuren, R. van Schaijk, M. Slotboom, P. Tello, P. Goarin, N. Akil, F. Neuilly, Z. Rittersma and A. Huerta</i>	
<b>A Novel SONOS Memory with HfSiON/Si3N4/HfSiON Stack for Improved Retention.....</b>	<b>45</b>
<i>R. van Schaijk, M. van Duuren, N. Akil, A. Huerta, S. Beckx, F. Neuilly, Z. Rittersma, M. Slotboom, S. Van Elshocht and J. Wouters</i>	

# Table of Contents

<b>Scalable Floating Gate Flash Memory Cell With Engineered Tunnel Dielectric and High-K (Al<sub>2</sub>O<sub>3</sub>) Interpoly Dielectric.....</b>	<b>47</b>
<i>Pieter Blomme, Joeri DeVos, Amal Akheyar, Luc Haspeslagh, Jan Van Houdt, Kristin De Meyer</i>	
<b>Charge Trapping Memory Cell of TANOS (Si-Oxide-SiN-Al<sub>2</sub>O<sub>3</sub>-TaN) Structure Compatible to Conventional NAND Flash Memory.....</b>	<b>49</b>
<i>Chang-Hyun Lee, Changseok Kang, Jaesung Sim, Jang-Sik Lee, Juhyung kim, Yoocheol Shin, Ki-Tae Park, Sanghun Jeon, Jongsun Sel, Younseok Jeong, Byeongin Choi, Viena Kim, Wonseok Jung, Chung-Il Hyun, Jungdal Choi and Kinam Kim</i>	
<b>Gate Disturb Reduction in a Silicon Nanocrystal Flash EEPROM by Means of Natural Threshold Voltage Reduction.....</b>	<b>51</b>
<i>Craig T. Swift, Alex Hoefler, Taras Kirichenko, Ramachandran Muralidhar, Erwin Prinz, Rajesh Rao, Glenn Rinkenberger, Michael Sadd, Robert Steimle</i>	
<b>Ultra High Density HfO<sub>2</sub> Nanodots Memory for Scaling.....</b>	<b>53</b>
<i>H. Wakai, M. Kobayashi, T. Kumise, M. Yamaguchi, T. Nakanishi and H. Tanaka</i>	
<b>90nm Split-Gate Nanocrystal Non-Volatile Memory with Reduced Threshold Voltage.....</b>	<b>55</b>
<i>Jane A. Yater, T. Kirichenko, E.J. Prinz, M. Sadd, R. Steimle, C.T. Swift, K-M. Chang</i>	
<b>90nm Embedded 2-Bit Per Cell Nanocrystal Flash EEPROM.....</b>	<b>57</b>
<i>Erwin J. Prinz, Jane Yater, Robert Steimle, Michael Sadd, Craig Swift, Ko-Min Chang</i>	
<b>Impact of Nanocrystal Size on NVM Array Reliability Performance.....</b>	<b>59</b>
<i>Horacio P. Gasquet, Robert F. Steimle, Rajesh A. Rao, Ramachandran Muralidhar</i>	
<b>Cycling Behavior of Nitride Charge Profile in NROM-type Memory Cells.....</b>	<b>61</b>
<i>A. Furnemont, M. Rosmeulen, J. Van Houdt, H. Maes, and K. De Meyer</i>	
<b>NROM Window Sensing for 2 and 4-bits per cell Products.....</b>	<b>63</b>
<i>Assaf Shappir, Eli Lusky, Guy Cohen, Boaz Eitan</i>	
<b>Ultra-uniform Threshold Voltage in SONOS-type Non-volatile Memory with Novel Charge Trap Layer Formed by Plasma Nitridation.....</b>	<b>65</b>
<i>Hiroshi Sunamura, Koji Masuzaki, Masayuki Terai, Setsu Kotsuji, Takashi Onizawa, Ayuka Morioka Taeko Ikarashi, Nobuyuki Ikarashi, Shinji Fujieda, and Hirohito Watanabe</i>	
<b>TWIn SONOS Transistor (TWISTOR) for 2-bit/cell SONOS Memory Technology.....</b>	<b>67</b>
<i>Byung Yong Choi, Byung-Gook Park, Jong Duk Lee, Hyungcheol Shin, Yong Kyu Lee, Suk-Kang Sung, Se-Hoon Lee, Heesoon Chae, Jong Jin Lee, Keun Hee Bai, Dong-Dae Kim, Dong-Won Kim, Choong-Ho Lee, and Donggun Park</i>	
<b>Extending Endurance of NROM Memories to Over 10 million Program/erase cycles.....</b>	<b>69</b>
<i>Yakov Roizin, Evgeny Pikhay, Michael Lisiansky, Alexey Heiman, Eli Alon, Efraim Aloni and Amos Fenigstein</i>	
<b>Highly Scalable NAND-type PHINES Flash Memory for Data Flash Applications.....</b>	<b>71</b>
<i>C.C. Yeh, Y.Y. Liao, W.J. Tsai, T.C. Lu, T.F. Ou, H.L. Kao, Tahui Wang, WenChi Ting, Joseph Ku, and Chih-Yuan Lu</i>	
<b>Quantitative Model for Data Retention Loss at NROM Nitride Charge Trapping Devices after Program / Erase Cycling.....</b>	<b>73</b>
<i>G. Tempel, R. Hagenbeck, M. Strassburg</i>	
<b>Programming Transients of Trapping Nitride Storage Flash Memory Cells and Evidence of Lateral Charge Redistributions during or after Programming.....</b>	<b>76</b>
<i>G. Tempel, W.v. Emden, R. Hagenbeck, P. Haibach, M. Isler, T. Mikolajick, T. Müller, S. Riedel, J.M. Schley, J. Schott, M. Strassburg, J. Willer</i>	
<b>New Model Proposed for Switching Mechanism of ReRAM.....</b>	<b>79</b>
<i>K. Kinoshita, T. Tamura, H. Aso, H. Noshiro, C. Yoshida, M.Aoki, Y. Sugiyama and H. Tanaka</i>	
<b>Resistance Switching of Al Doped ZnO for Non Volatile Memory Applications.....</b>	<b>81</b>
<i>Dongsoo Lee, Dae-Kue Hwang, Man Chang, Yunik Son, Dong-jun Seong, Dooho Choi, Hyunsang Hwang</i>	
<b>Excellent Resistance Switching Characteristics of Pt/Single-crystal Nb-Doped SrTiO<sub>3</sub> Schottky Junction.....</b>	<b>83</b>
<i>Hyunjun Sim, Dong-jun Seong, Man Chang and Hyunsang Hwang</i>	

# Table of Contents

<b>Enhanced Switching Reliability of a Non-volatile Phase-Change Memory Device with an Oxidized TiN Electrode</b> .....	<b>85</b>
<i>Dae-Hwan Kang, In Ho Kim, Jeung-hyun Jeong, Byung-ki Cheong, Dong-Ho Ahn, and Ki-Bum Kim</i>	
<b>Generalized Phase Change Memory Scaling Rule Analysis</b> .....	<b>87</b>
<i>SangBum Kim, H.-S. Philip Wong</i>	
<b>Nonvolatile SRAM based on Phase Change</b> .....	<b>90</b>
<i>Masashi Takata, Kazuya Nakayama, Takatomi Izumi, Toru Shinmura, Junichi Akita and Akio Kitagawa</i>	
<b>Thermal Stress Evaluation of a PCRAM Material Ge<sub>2</sub>Sb<sub>2</sub>Te<sub>5</sub></b> .....	<b>92</b>
<i>K.N. Chen, L Krusin-Elbaum, C. Cabral Jr. , C. Lavoie, J. Sun, S. Rossnagel</i>	